

•Outline TO-247GE

Inner Circuit

(1) C

Type

(2)

(3)

Reel Size (mm)

Packing Code

Marking

Tape Width (mm)

Basic Ordering Unit (pcs)

Packaging Specifications
Packaging

(1)(2)(3)

650V 30A Field Stop Trench IGBT

(1) Gate(2) Collector

(3) Emitter

*1 Built in FRD

Tube

-

-

600

C13

RGTV60TS65D

V _{CES}	650V
I _{C(100°C)}	30A
V _{CE(sat) (Typ.)}	1.5V
P _D	194W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching & Low Switching Loss
- 3) Short Circuit Withstand Time 2µs
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating ; RoHS Compliant

Applications

Solar Inverter

UPS

Welding

IH

PFC

•Absolute Maximum Ratings (at T_c = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Oursent	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	60	А
Collector Current	T _C = 100°C	Ι _C	30	А
Pulsed Collector Current	I _{CP} *1	120	А	
Diode Forward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	I _F	56	А
Diode Forward Current	T _C = 100°C	I _F	30	А
Diode Pulsed Forward Current		I _{FP} ^{*1}	120	А
Power Dissinction	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	194	W
Power Dissipation	T _C = 100°C	P _D	97	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by T_{jmax.}

RGTV60TS65DGC13

Thermal Resistance

Parameter	Symbol	Values			Unit
Faranieter	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.77	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	1.17	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Farameter	Symbol Conditions		Min.	Тур.	Max.	Unit	
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V	
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA	
Gate - Emitter Leakage Current	I _{GES}	V_{GE} = ±30V, V_{CE} = 0V	-	-	±200	nA	
Gate - Emitter Threshold Voltage	V _{GE(th)}	$V_{CE} = 5V, I_C = 21.0mA$	5.0	6.0	7.0	V	
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 30A, V_{GE} = 15V$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.5 1.85	1.9 -	V	

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deveneter	Symbol Conditions	Conditions		l lus it		
Parameter		Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1730	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	74	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	30	-	
Total Gate Charge	Qg	V _{CE} = 400V	-	64	-	
Gate - Emitter Charge	Q _{ge}	I _C = 30A	-	14	-	nC
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	24	-	
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 30$ A, $V_{\rm CC} = 400$ V	-	33	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	12	-	
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	105	-	ns
Fall Time	t _f	Inductive Load	-	40	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.57	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.50	-	mJ
Turn - on Delay Time	t _{d(on)}	$I_{\rm C} = 30$ A, $V_{\rm CC} = 400$ V	-	32	-	
Rise Time	t _r	V_{GE} = 15V, R_G = 10 Ω	-	13	-	
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	121	-	ns
Fall Time	t _f	Inductive Load	-	80	-	
Turn - on Switching Loss	E _{on}	*E _{on} includes diode	-	0.63	-	
Turn - off Switching Loss	E _{off}	reverse recovery	-	0.72	-	mJ
		$I_{\rm C} = 120$ A, $V_{\rm CC} = 520$ V				
Reverse Bias Safe Operating Area	RBSOA	$V_{P} = 650V, V_{GE} = 15V$	FU	LL SQUA	RE	-
		R _G = 100Ω, T _j = 175°C				
		$V_{CC} \leq 360V$				
Short Circuit Withstand Time	t _{sc}	V _{GE} = 15V	2	-	-	μs
		$T_j = 25^{\circ}C$				

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Unit
		I _F = 30A				
Diode Forward Voltage	V_{F}	T _j = 25°C	-	1.45	1.9	V
		T _j = 175°C	-	1.55	-	
Diode Reverse Recovery Time	t _{rr}		-	95	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	I _F = 30A V _{CC} = 400V	-	8.1	-	A
Diode Reverse Recovery Charge	Q _{rr}	di _F /dt = 200A/µs T _j = 25°C	-	0.42	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	19.3	-	μJ
Diode Reverse Recovery Time	t _{rr}		-	155	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	$I_F = 30A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	10.4	-	A
Diode Reverse Recovery Charge	Q _{rr}		-	0.95	-	μC
Diode Reverse Recovery Energy	Err		-	62.5	-	μJ

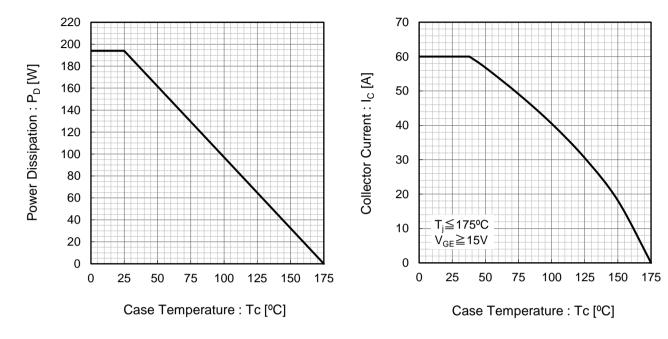
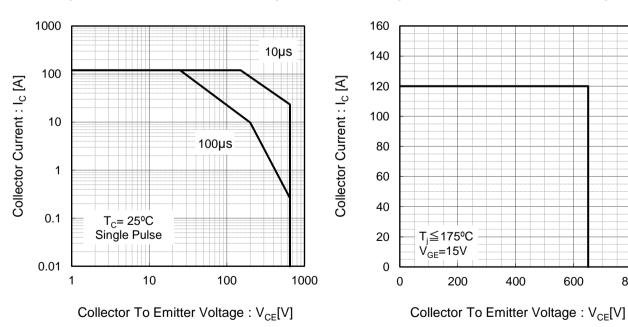


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area



800

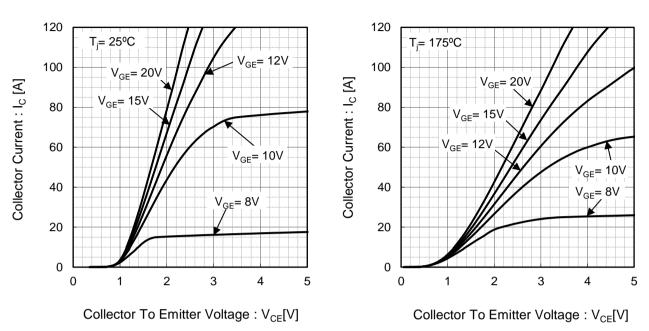
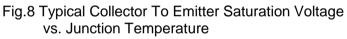


Fig.5 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics



 $I_{c} = 60A$

 $I_{C} = 30A$

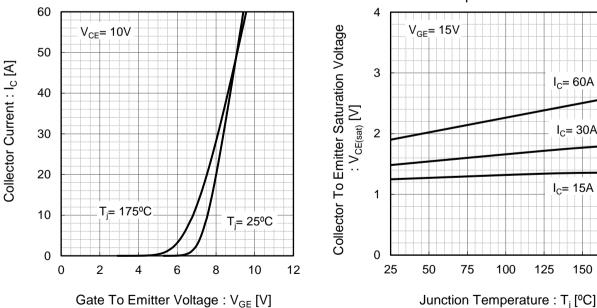
I_C= 15A

150

175

125

Fig.6 Typical Output Characteristics



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Fig.10 Typical Collector To Emitter Saturation Voltage

•Electrical Characteristic Curves

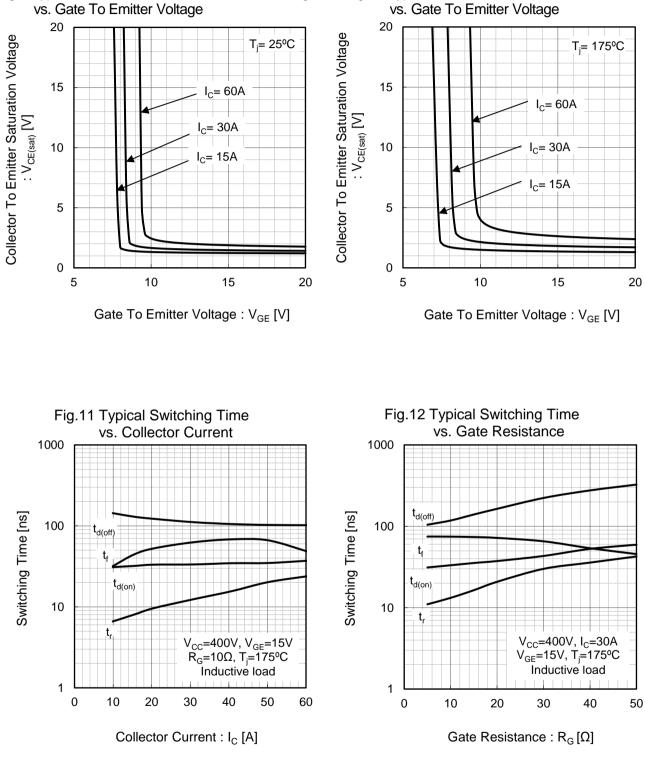
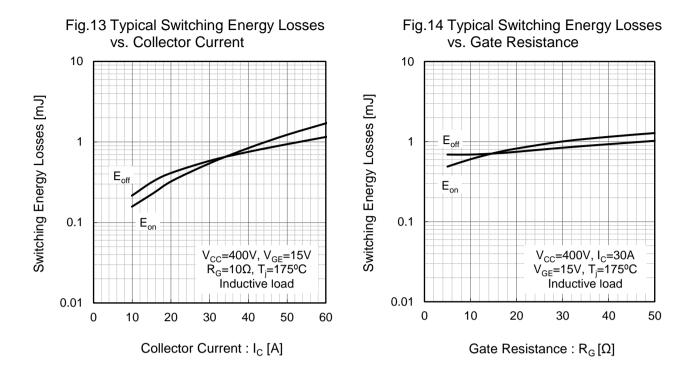
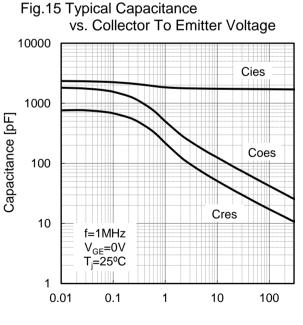


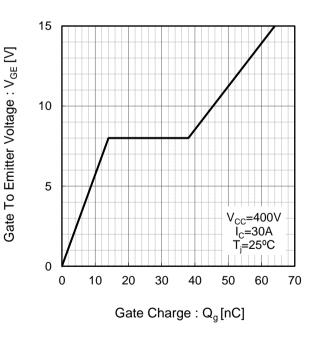
Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage





Collector To Emitter Voltage : V_{CE}[V]

Fig.16 Typical Gate Charge



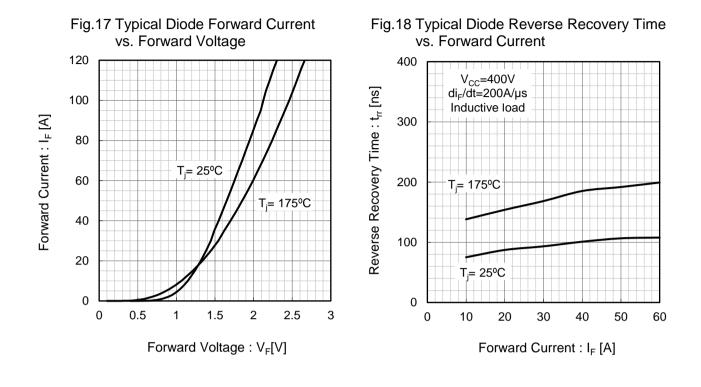


Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

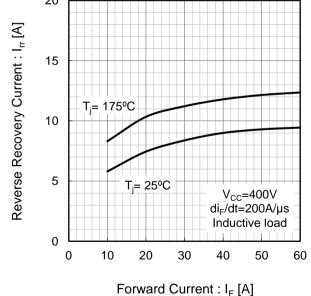
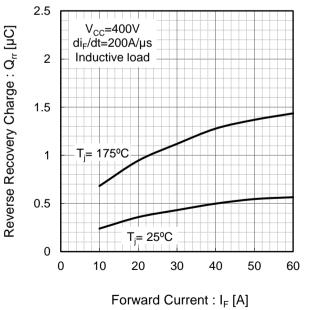


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



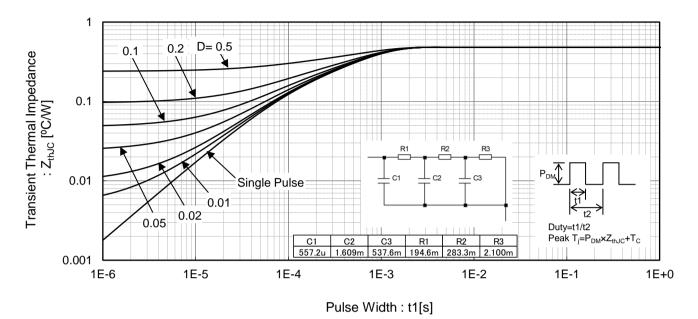
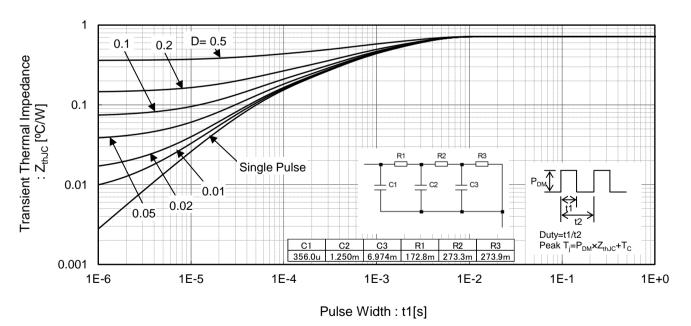


Fig.21 Typical IGBT Transient Thermal Impedance





●Inductive Load Switching Circuit and Waveform

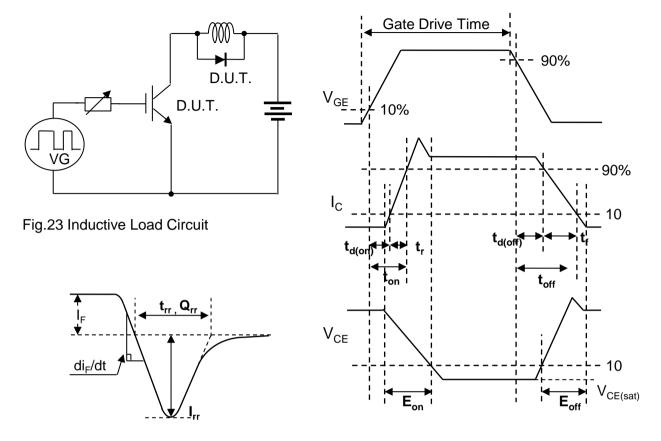


Fig.25 Diode Reverce Recovery Waveform

Fig.24 Inductive Load Waveform



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